



Everspin Demonstrates World's First CXL-Connected MRAM at SNIA Developer Conference 2026

September 29, 2026

Working platform delivers memory-semantic access with writes up to 100x faster than NAND-based solid-state storage and is ready for customer workload testing

CHANDLER, Ariz.--(BUSINESS WIRE)--Sep. 29, 2026-- Everspin Technologies, Inc. (NASDAQ: MRAM), a leading developer and manufacturer of MRAM persistent memory solutions, announced today the successful demonstration of the world's first Compute Express Link (CXL)-connected MRAM platform at SNIA Developer Conference (SDC) 2026. The demo added a fast persistent memory tier between DRAM and NAND storage that can reduce the time processors and accelerators spend waiting for data and help AI systems run at higher utilization.

The working system connects [Everspin PERSYST MRAM](#) to CXL-enabled platforms as persistent memory with memory semantics, combining CXL's standard high-speed connectivity with MRAM's ability to retain data without power. It creates a fast persistent buffer and cache tier with cache-line-level, nanosecond-class access and writes up to 100x faster than NAND-based solid-state storage. Data remains available through a power interruption or system restart without relying on battery-backed DRAM or having to first flush data to an SSD.

The demo uses a Supermicro AS-1116CS-TN server with an AMD EPYC 9355 32-core processor, an AMD Alveo U250 FPGA platform with a Wolley CXL controller and Everspin PERSYST 1GB DDR4 MRAM UDIMMs. The configuration provides an open standards-based platform for demonstrating coherent access to persistent MRAM through CXL. It also enables memory resources to be pooled and shared across hosts, allowing persistent memory capacity to be allocated where workloads need it. For AI systems, that creates opportunities for applications such as checkpointing and persistent key-value (KV) cache.

"Everspin has been working with data center customers for 15 years, and we continue to innovate as AI changes the memory needs of systems," said Sanjeev Aggarwal, president and CEO of Everspin Technologies. "CXL gives us a standard way to bring persistent MRAM to a much broader range of compute platforms. We now have a working system so customers can run their own workloads and measure the benefit for their specific applications."

At SDC, Everspin and Wolley demonstrated read and write access to MRAM through the CXL interface under demanding test conditions.

"Wolley enables memory and storage connectivity through CXL, and this demonstration with Everspin shows how persistent MRAM can be brought into that environment with memory semantics," said Dr. Bernard Shung, CEO of Wolley. "Together, we are demonstrating a practical way to connect persistent memory through CXL and make it available to today's compute platforms."

The SDC demonstration builds on Everspin's work to extend MRAM into new memory architectures, including persistent caching, write buffering and metadata applications. To learn more about Everspin MRAM for data center applications, visit [the Everspin Data Centers page](#).

About Everspin Technologies

Everspin Technologies, Inc., is the world's leading provider of Magnetoresistive RAM (MRAM). Everspin MRAM delivers the industry's most robust, highest-performance, non-volatile memory for Industrial IoT, Data Centers, and other mission-critical applications where data persistence is paramount. Headquartered in Chandler, Arizona, Everspin provides commercially available MRAM solutions to a large and diverse customer base. For more information, visit www.everspin.com

Cautionary Statement Regarding Forward-Looking Statements

This press release contains forward-looking statements regarding future events or results. Forward-looking statements are identified by words such as "will," "expects" or similar expressions and include, but are not limited to, statements regarding Everspin's anticipated business plans and business strategy. These forward-looking statements are subject to known and unknown risks, uncertainties, assumptions, and other factors that may cause actual results or outcomes to be materially different from any future results or outcomes expressed or implied by the forward-looking statements, including, without limitation, the risks set forth under the caption "Risk Factors" in Everspin's Annual Report on Form 10-K for the year ended December 31, 2025 filed with the SEC on March 5, 2026, as well as in Everspin's subsequent filings with the SEC. Any forward-looking statements made by

Everspin in this press release speak only as of the date on which they are made, and subsequent events may cause these expectations to change. Everspin disclaims any obligations to update or alter these forward-looking statements in the future, whether as a result of new information, future events or otherwise, except as required by law.

View source version on businesswire.com: <https://www.businesswire.com/news/home/20260929225389/en/>

Media Contact:

Everspin Technologies

Stephanie Quinn

T: 480-316-8370

E: stephanie.quinn@everspin.com

Source: Everspin Technologies, Inc.